

Title (en)

METHOD AND APPARATUS FOR PHOTO-EXCITATION OF CHEMICALS FOR ATOMIC LAYER DEPOSITION OF DIELECTRIC FILM

Title (de)

VERFAHREN UND VORRICHTUNG ZUR LICHTANREGUNG VON CHEMISCHEN STOFFEN FÜR ATOMSCHICHTABSCHIEDUNG EINES DIELEKTRISCHEN FILMS

Title (fr)

PROCEDE ET APPAREIL POUR LA PHOTO-EXCITATION DE PRODUITS CHIMIQUES POUR UN DEPOT PAR COUCHE ATOMIQUE D'UN FILM DIELECTRIQUE

Publication

**EP 2022084 A2 20090211 (EN)**

Application

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Abstract (en)

[origin: US2007259111A1] The invention generally provides a method for depositing materials, and more particularly, embodiments of the invention relate to chemical vapor deposition processes and atomic layer deposition processes utilizing photoexcitation techniques to deposit barrier layers, seed layers, conductive materials, and dielectric materials. Embodiments of the invention generally provide methods of the assisted processes and apparatuses, in which the assisted processes may be conducted for providing uniformly deposited material.

IPC 8 full level

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